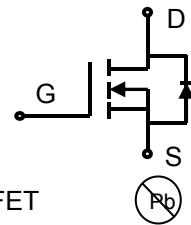


Lonten N-channel 500V, 5A Power MOSFET

Description	Product Summary
The Power MOSFET is fabricated using the advanced planar VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.	V_{DSS} 500V I_D 5A $R_{DS(on),max}$ 1.6Ω $Q_{g,typ}$ 12.8 nC
Features	
<ul style="list-style-type: none"> ◆ Low $R_{DS(on)}$ ◆ Low gate charge (typ. $Q_g = 12.8$ nC) ◆ 100% UIS tested ◆ RoHS compliant 	
Applications	 <ul style="list-style-type: none"> ◆ Power factor correction. ◆ Switched mode power supplies. ◆ LED driver.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	500	V
Continuous drain current ($T_c = 25^\circ C$) ($T_c = 100^\circ C$)	I_D	5 3.1	A A
Pulsed drain current ¹⁾	I_{DM}	20	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	210	mJ
Peak diode recovery dv/dt ³⁾	dv/dt	5	V/ns
Power Dissipation TO-220F ($T_c = 25^\circ C$) Derate above $25^\circ C$	P_D	30 0.24	W W/ $^\circ C$
Power Dissipation TO-220\TO-251\TO-252 ($T_c = 25^\circ C$) Derate above $25^\circ C$		75 0.6	W W/ $^\circ C$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	$^\circ C$
Continuous diode forward current	I_S	5	A
Diode pulse current	$I_{S,pulse}$	20	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-220\TO-251\TO-252	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	4.17	1.67	$^\circ C/W$
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	110	$^\circ C/W$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Reel
LNC5N50	TO-220	LNC5N50	50	
LND5N50	TO-220F	LND5N50	50	
LNG5N50	TO-252	LNG5N50		3000
LNH5N50	TO-251	LNH5N50	80	

Electrical Characteristics

T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	500	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25 mA	2	-	4	V
Drain cut-off current	I _{DSS}	V _{DS} =500 V, V _{GS} =0 V, T _j = 25°C T _j = 125°C	-	-	1 100	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =2.5 A	-	1.35	1.60	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	537.5	-	pF
Output capacitance	C _{oss}		-	80.3	-	
Reverse transfer capacitance	C _{rss}		-	4	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 250 V, I _D = 5 A R _G = 10 Ω, V _{GS} =15 V	-	10.3	-	ns
Rise time	t _r		-	33.1	-	
Turn-off delay time	t _{d(off)}		-	29.4	-	
Fall time	t _f		-	13.2	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =400 V, I _D =5 A, V _{GS} =0 to 10 V	-	3.9	-	nC
Gate to drain charge	Q _{gd}		-	4.6	-	
Gate charge total	Q _g		-	12.8	-	
Gate plateau voltage	V _{plateau}		-	5	-	
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =5 A	-	-	1.5	V
Reverse recovery time	t _{rr}	V _R =250 V, I _F =5 A, dI _F /dt=100 A/μs	-	319.2	-	ns
Reverse recovery charge	Q _{rr}		-	1.6	-	
Peak reverse recovery current	I _{rrm}		-	10.2	-	

Notes:

1. Pulse width limited by maximum junction temperature.
2. L=10mH, I_{AS} = 6.5A, Starting T_j= 25°C.
3. I_{SD} = 5A, dI/dt≤100A/us, V_{DD}≤BV_{DS}, Starting T_j= 25°C.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

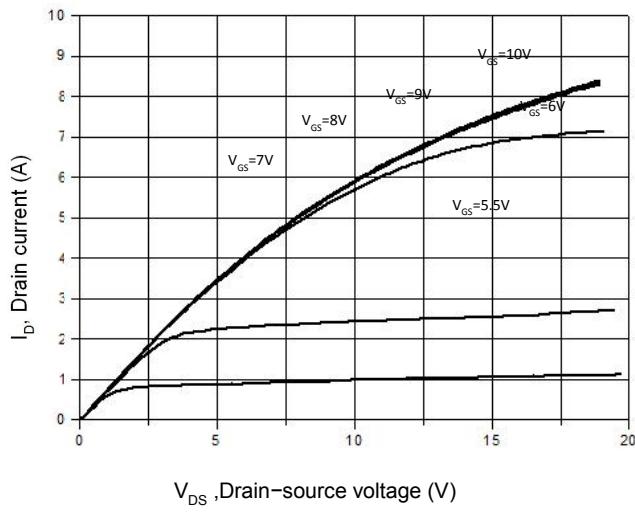


Figure 2. Transfer Characteristics

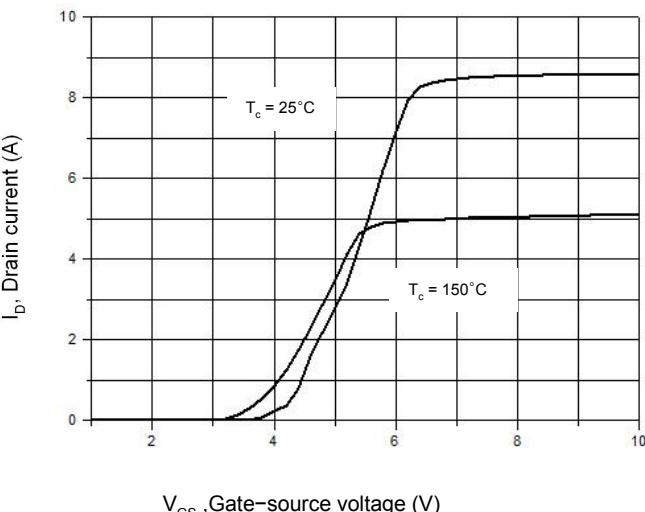


Figure 3. On-Resistance Variation vs. Drain Current

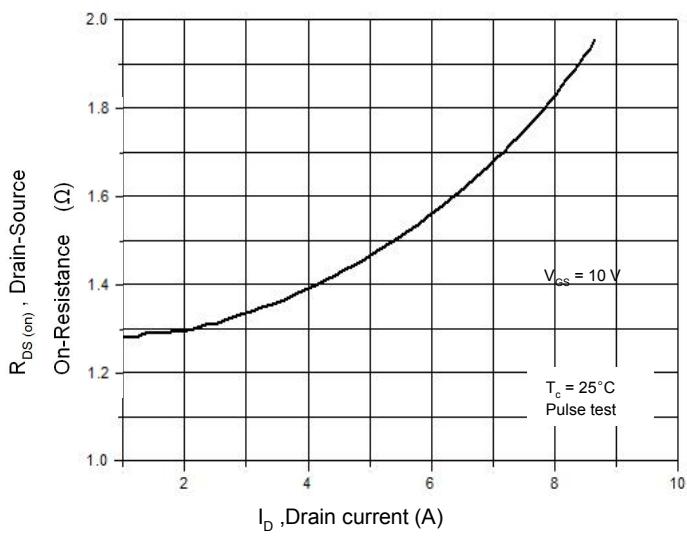


Figure 4. Threshold Voltage vs. Temperature

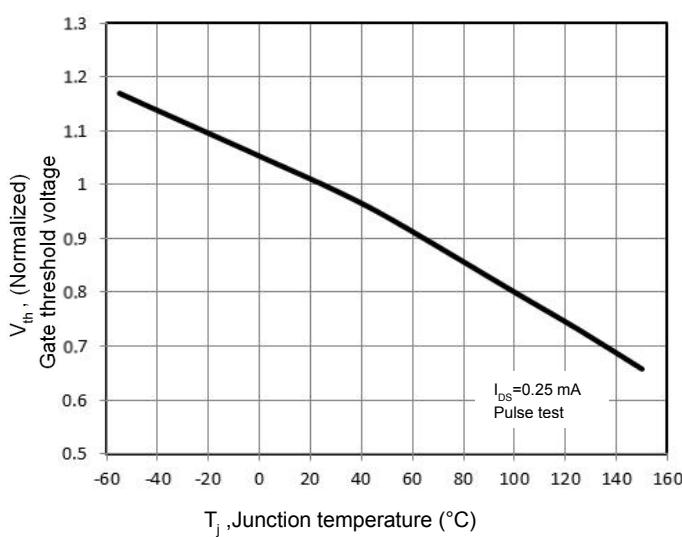


Figure 5. Breakdown Voltage vs. Temperature

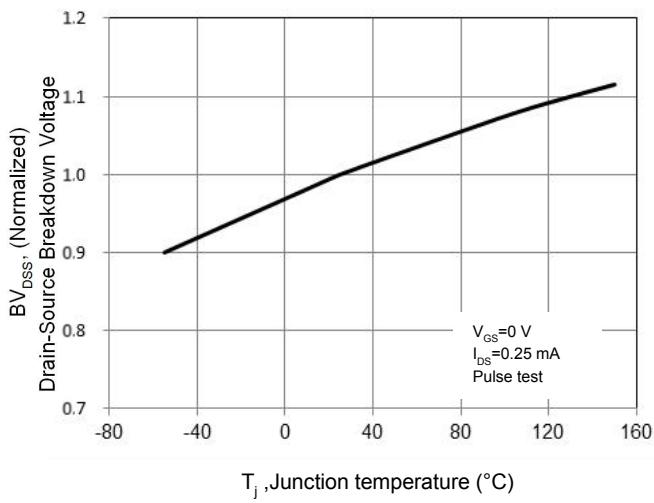


Figure 6. On-Resistance vs. Temperature

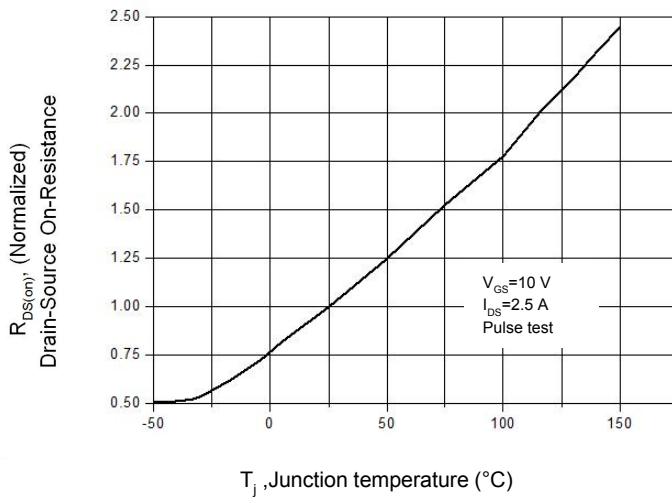


Figure 7. Capacitance Characteristics

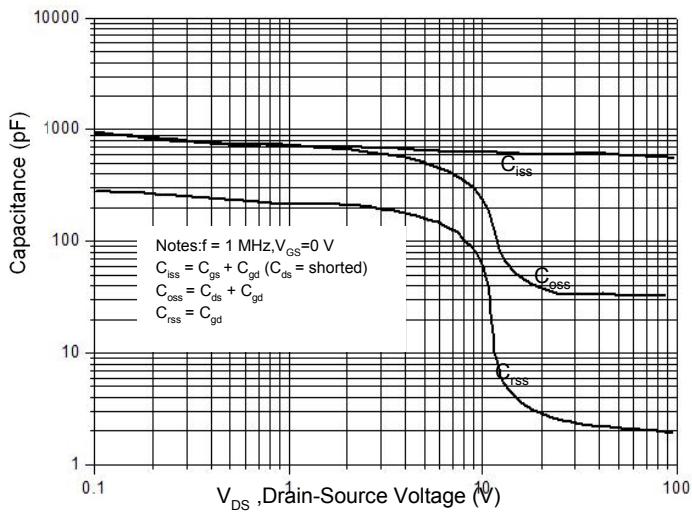


Figure 9. Maximum Safe Operating Area

TO-220F

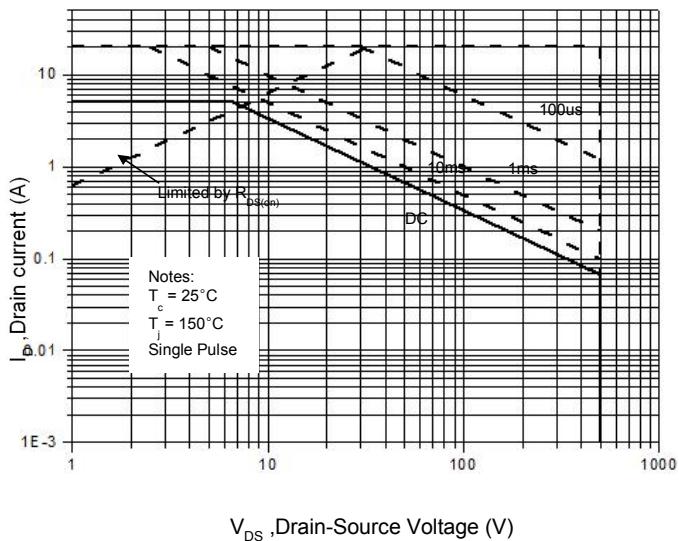


Figure 11. Power Dissipation vs. Temperature

TO-220F

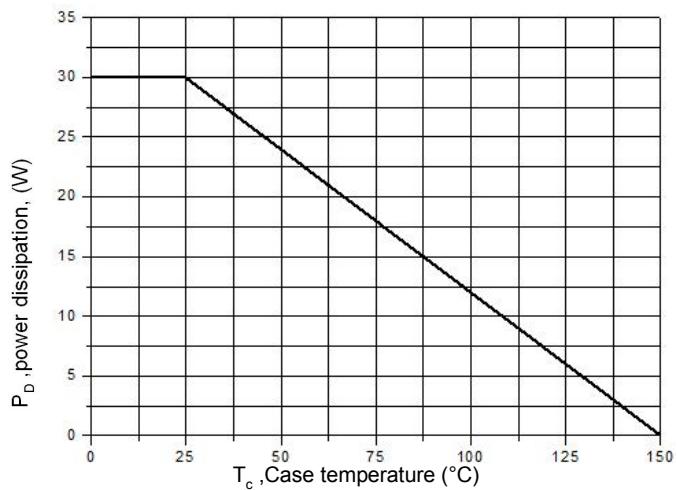


Figure 8. Gate Charge Characteristics

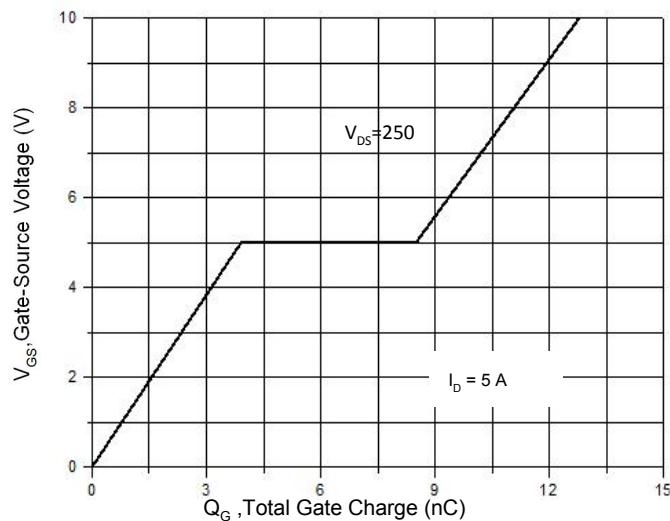


Figure 10. Maximum Safe Operating Area

TO-220/TO-251/TO-252

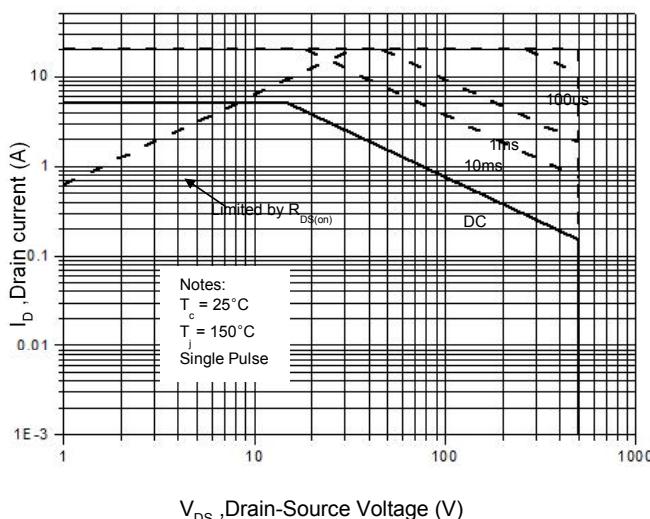


Figure 12. Power Dissipation vs. Temperature

TO-220/TO-251/TO-252

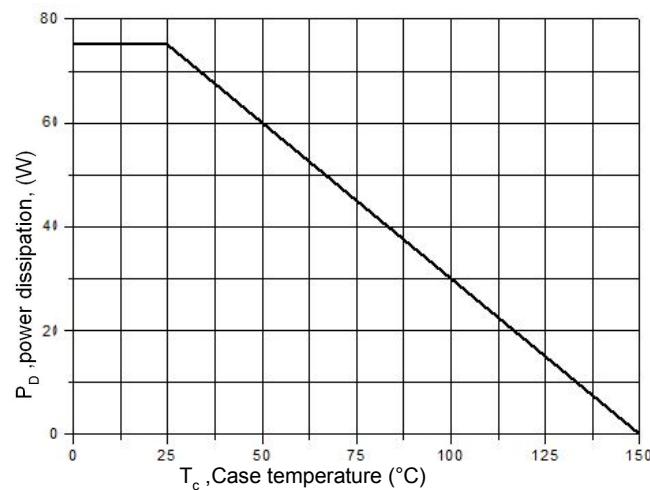


Figure 13. Continuous Drain Current vs. Temperature

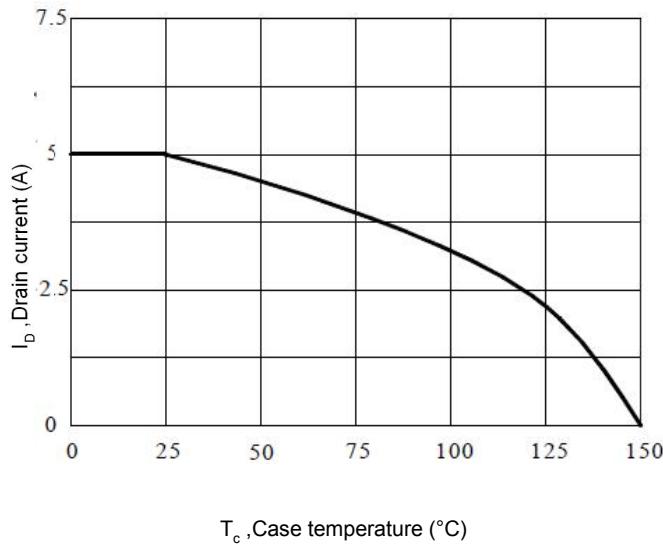


Figure 14. Body Diode Transfer Characteristics

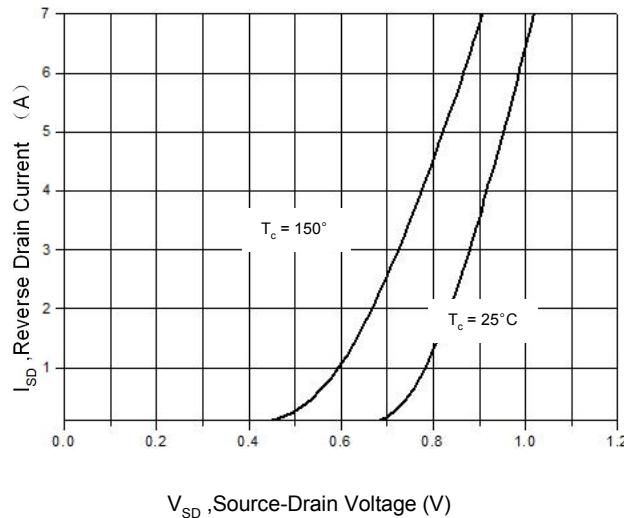


Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

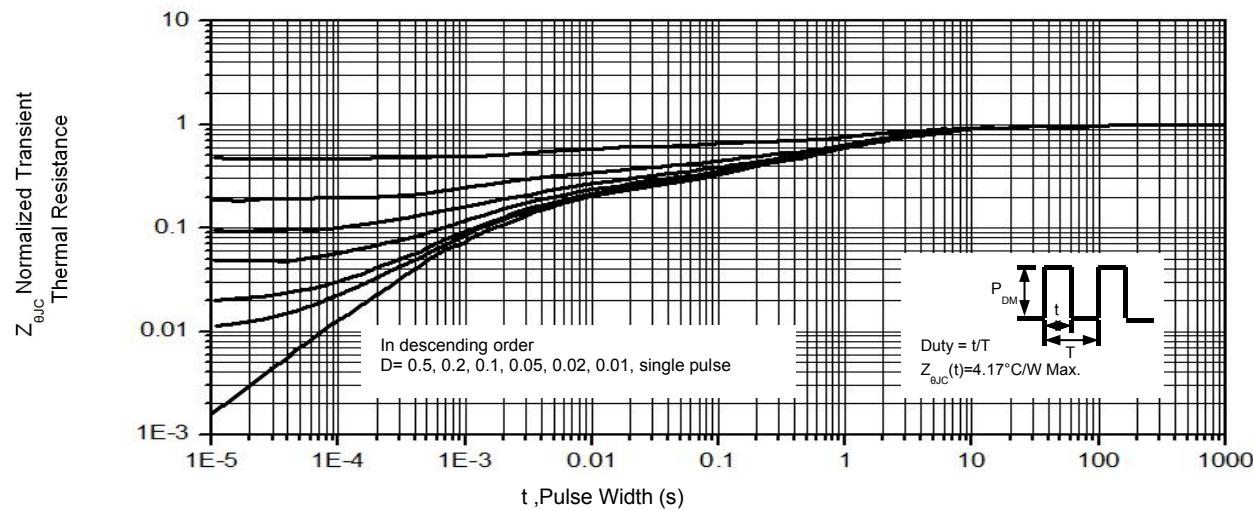
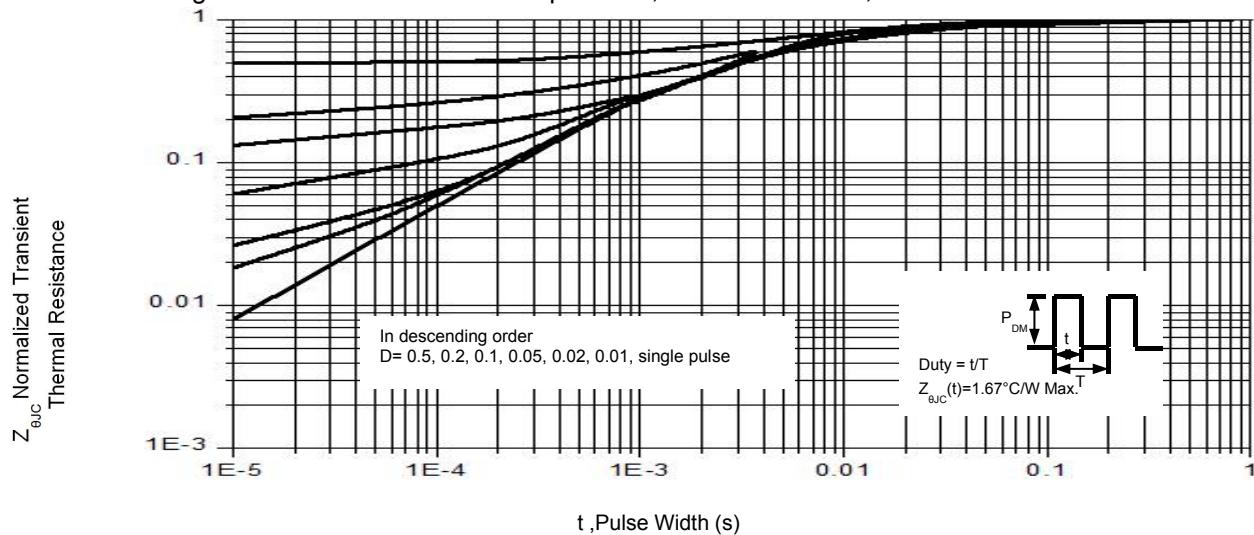
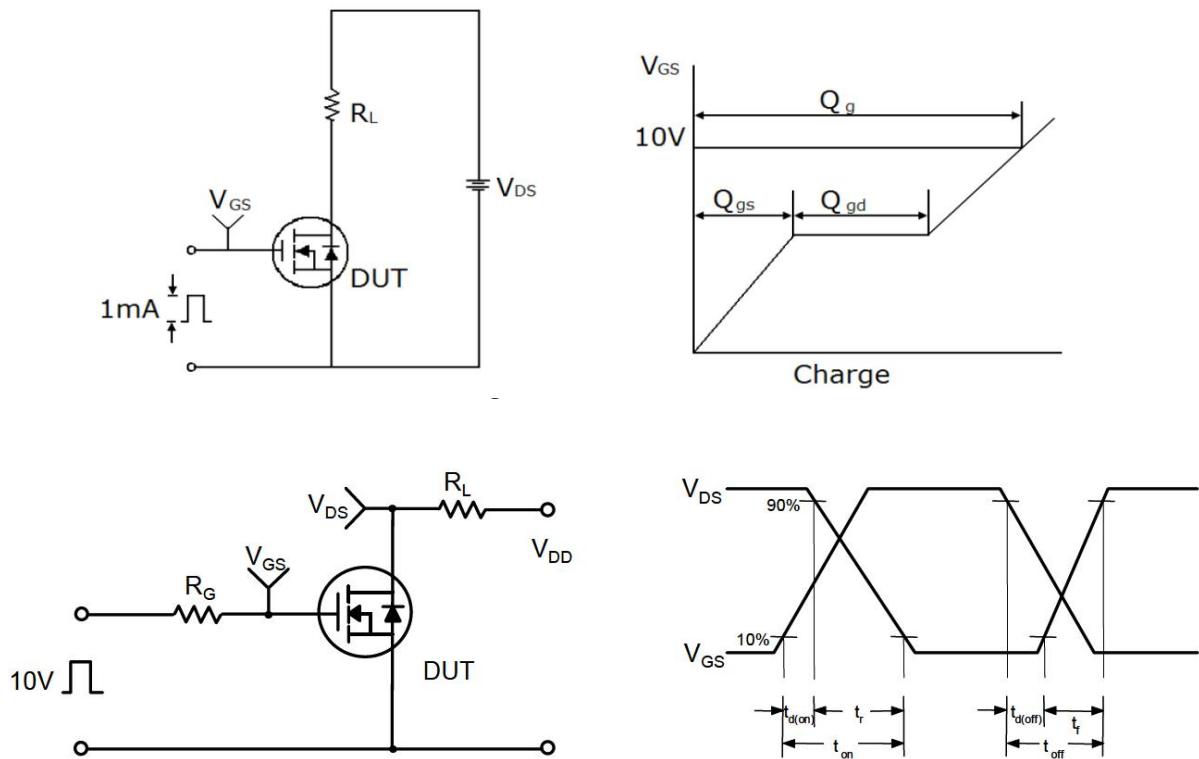


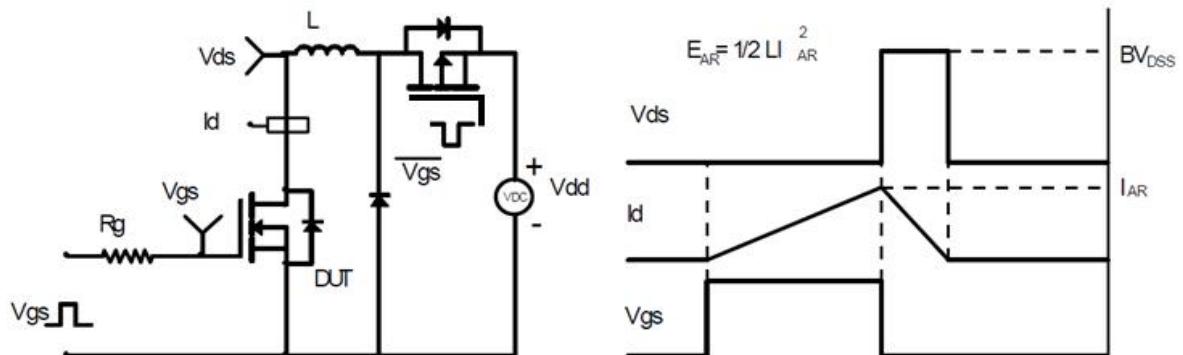
Figure 16. Transient Thermal Impedance, Junction to Case, TO-220/TO-251/TO-252



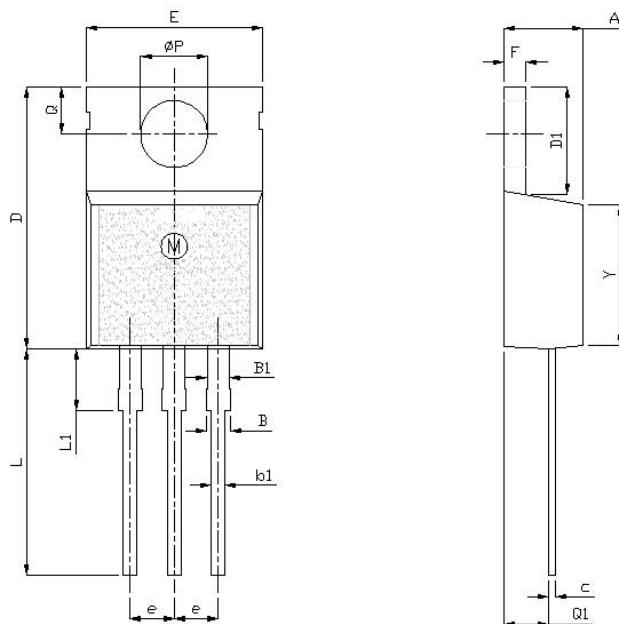
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms



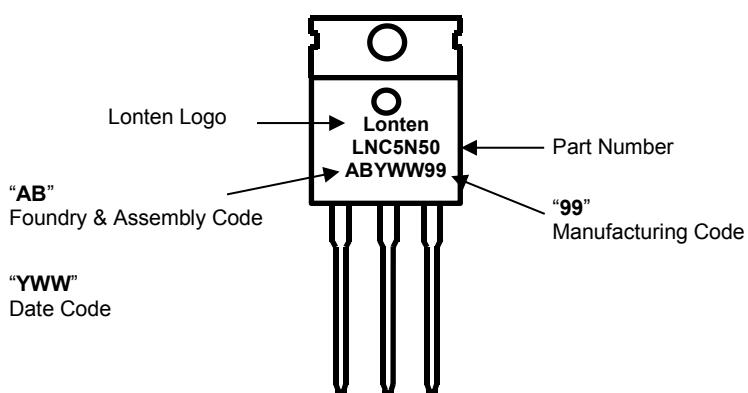
Mechanical Dimensions for TO-220



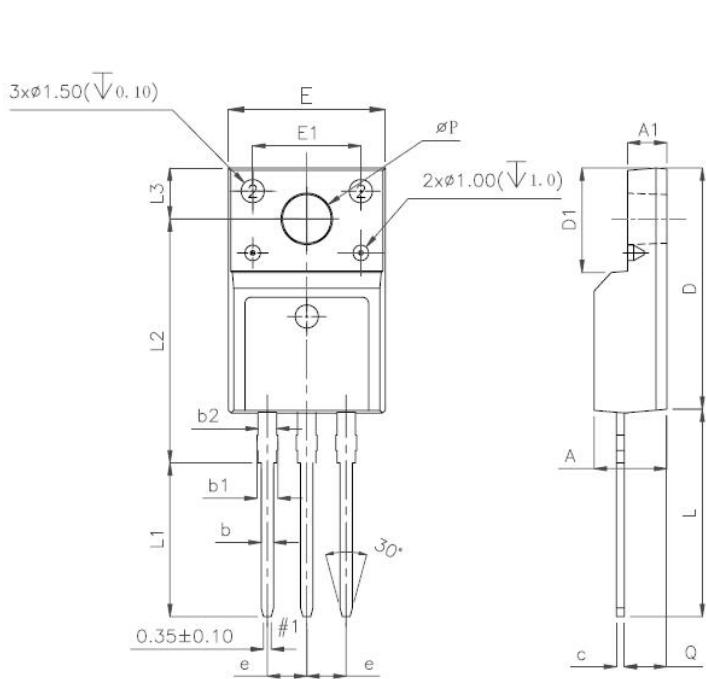
UNIT: mm

SYMBOL	MIN	NOM	MAX
A	4		4.8
B	1.2		1.4
B1	1		1.4
b1	0.75		0.95
c	0.4		0.55
D	15		16.5
D1	5.9		6.9
E	9.9		10.7
e	2.44	2.54	2.64
F	1.1		1.4
L	12.5		14.5
L1	3	3.5	4
ΦP	3.7	3.8	3.9
Q	2.5		3
Q1	2		2.9
Y	8.02	8.12	8.22

TO-220 Part Marking Information

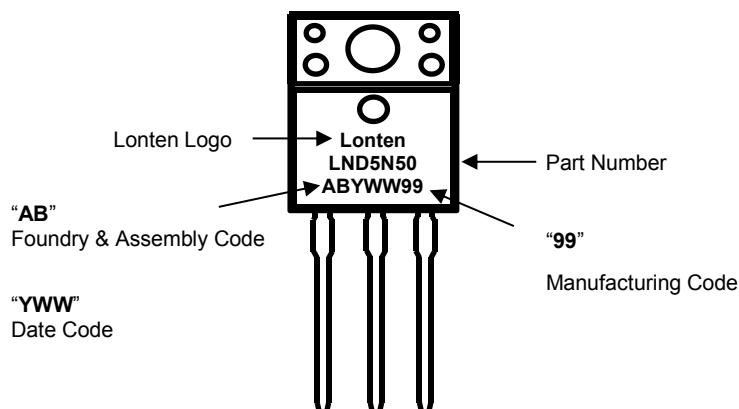


Mechanical Dimensions for TO-220F

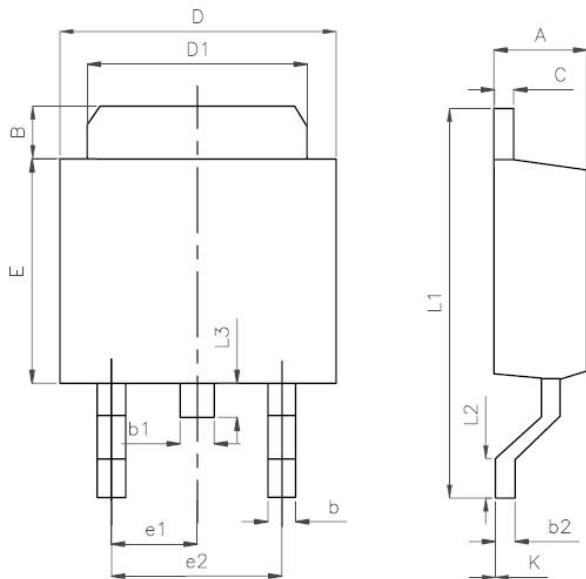


UNIT: mm			
SYMBOL	MIN	NOM	MAX
A	4.5		4.9
A1	2.3		2.9
b	0.65		0.9
b1	1.1		1.7
b2	1.2		1.4
c	0.35		0.65
D	14.5		16.5
D1	6.1		6.9
E	9.6		10.3
E1	6.5	7	7.5
e	2.44	2.54	2.64
L	12.5		14.3
L1	9.45		10.05
L2	15		16
L3	3.2		4.4
ØP	3		3.3
Q	2.5		2.9

TO-220F Part Marking Information



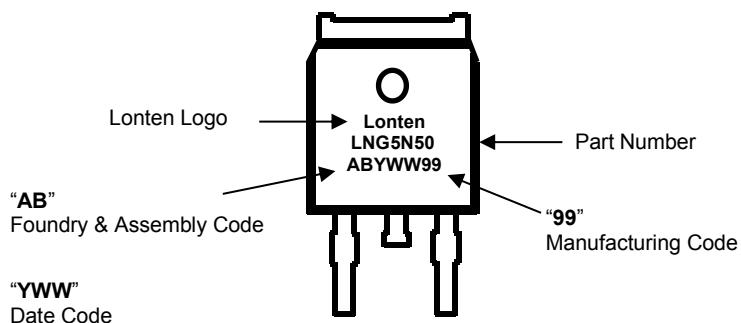
Mechanical Dimensions for TO-252



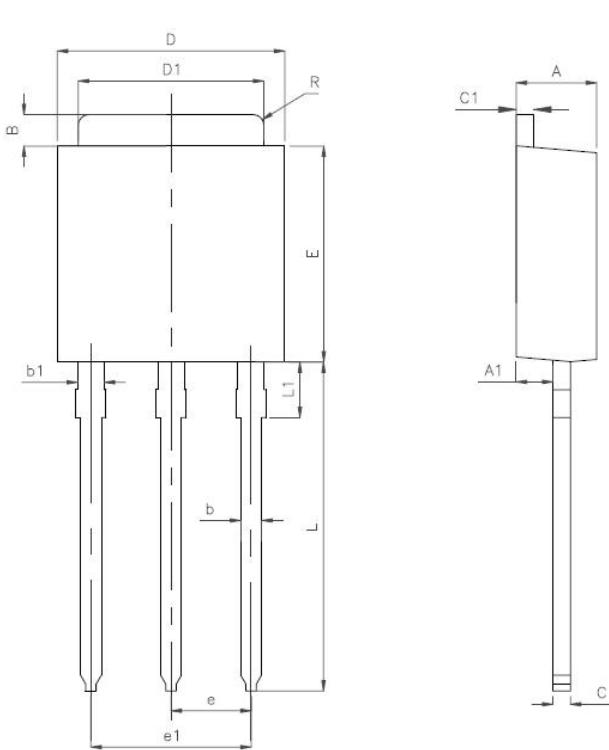
UNIT: mm

SYMBOL	MIN	NOM	MAX
A	2.10		2.50
B	0.80		1.25
b	0.50		0.85
b1	0.50		0.90
b2	0.45		0.60
C	0.45		0.60
D	6.35		6.75
D1	5.10		5.50
E	5.80		6.30
e1	2.25	2.30	2.35
e2	4.45		4.75
L1	9.50		10.20
L2	0.90		1.45
L3	0.60		1.10
K	-0.1		0.10

TO-252 Part Marking Information

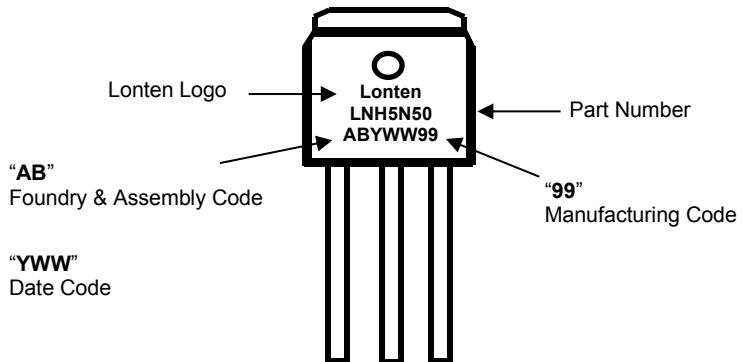


Mechanical Dimensions for TO-251



UNIT: mm			
SYMBOL	MIN	NOM	MAX
A	2.10		2.50
A1	0.95		1.30
B	0.80		1.25
b	0.50		0.80
b1	0.70		0.90
C	0.45		0.60
C1	0.45		0.60
D	6.35		6.75
D1	5.10		5.50
E	5.80		6.30
e	2.25	2.30	2.35
L	7.70		8.50
L1	1.45		1.95
R		0.30	

TO-251 Part Marking Information



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